

**Notice of References Cited**

Application/Control N

09/670,520

Applicant(s)/Patent Under  
Reexamination  
MORIYAMA ET AL.

Examiner

Granvill D Lee, Jr

Art Unit

2825

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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